

(12) **United States Patent**  
**Koifman et al.**

(10) **Patent No.:** **US 9,571,774 B2**  
(45) **Date of Patent:** **Feb. 14, 2017**

(54) **CURRENT MODE PIXEL AND READOUT CIRCUIT HAVING A FIRST AND A SECOND READOUT PHASE**

USPC ..... 250/214 R, 208.1  
See application file for complete search history.

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(\* ) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 42 days.

(57) **ABSTRACT**

A device comprising a pixel, a current source, and a readout circuit; wherein during a first readout phase of the pixel, the readout circuit is configured to sample a sampled output voltage of an output node of the pixel; and wherein an output current of the pixel is set by the current source; wherein between the first readout phase of the pixel and a second readout phase of the pixel, the pixel is configured to change the output current to provide a second output current, wherein the change of the output current is responsive to radiation sensed by a radiation sensor of the pixel during a sensing period; wherein during the second readout phase of the pixel the readout circuit is configured to sample the second output current while providing the sampled output voltage to the output node of the pixel; wherein during the first readout phase of the pixel and the second readout phase of the pixel a drain source voltage of an output transistor of the pixel is maintained constant; and wherein the output transistor is configured to generate the second output current.

(21) Appl. No.: **14/849,805**

(22) Filed: **Sep. 10, 2015**

(65) **Prior Publication Data**

US 2016/0240572 A1 Aug. 18, 2016

**Related U.S. Application Data**

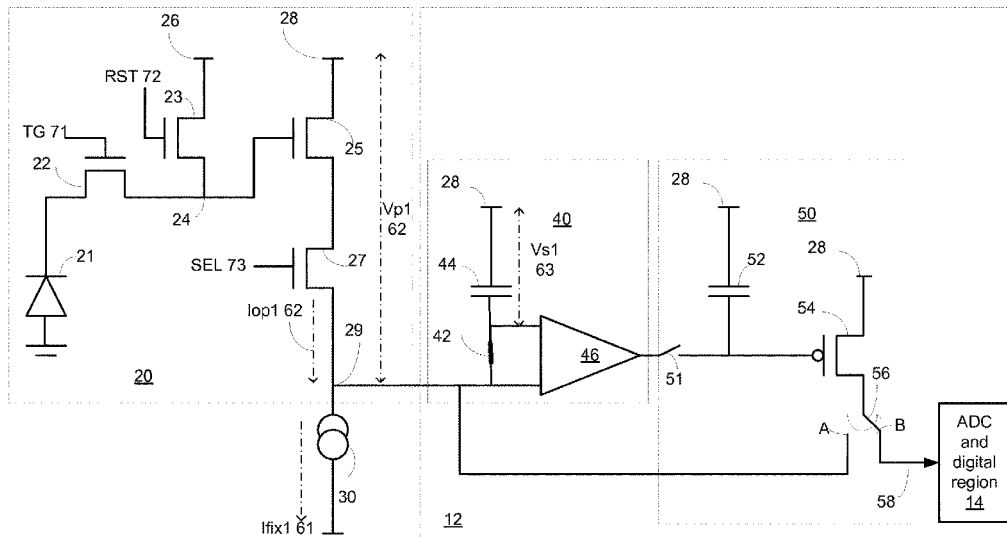
(60) Provisional application No. 62/115,337, filed on Feb. 12, 2015.

(51) **Int. Cl.**  
**H04N 5/378** (2011.01)

(52) **U.S. Cl.**  
CPC ..... **H04N 5/378** (2013.01)

(58) **Field of Classification Search**  
CPC ..... H04N 5/378; H04N 5/3745; H04N 3/14;  
G06F 3/0412; H01L 27/146

**18 Claims, 8 Drawing Sheets**



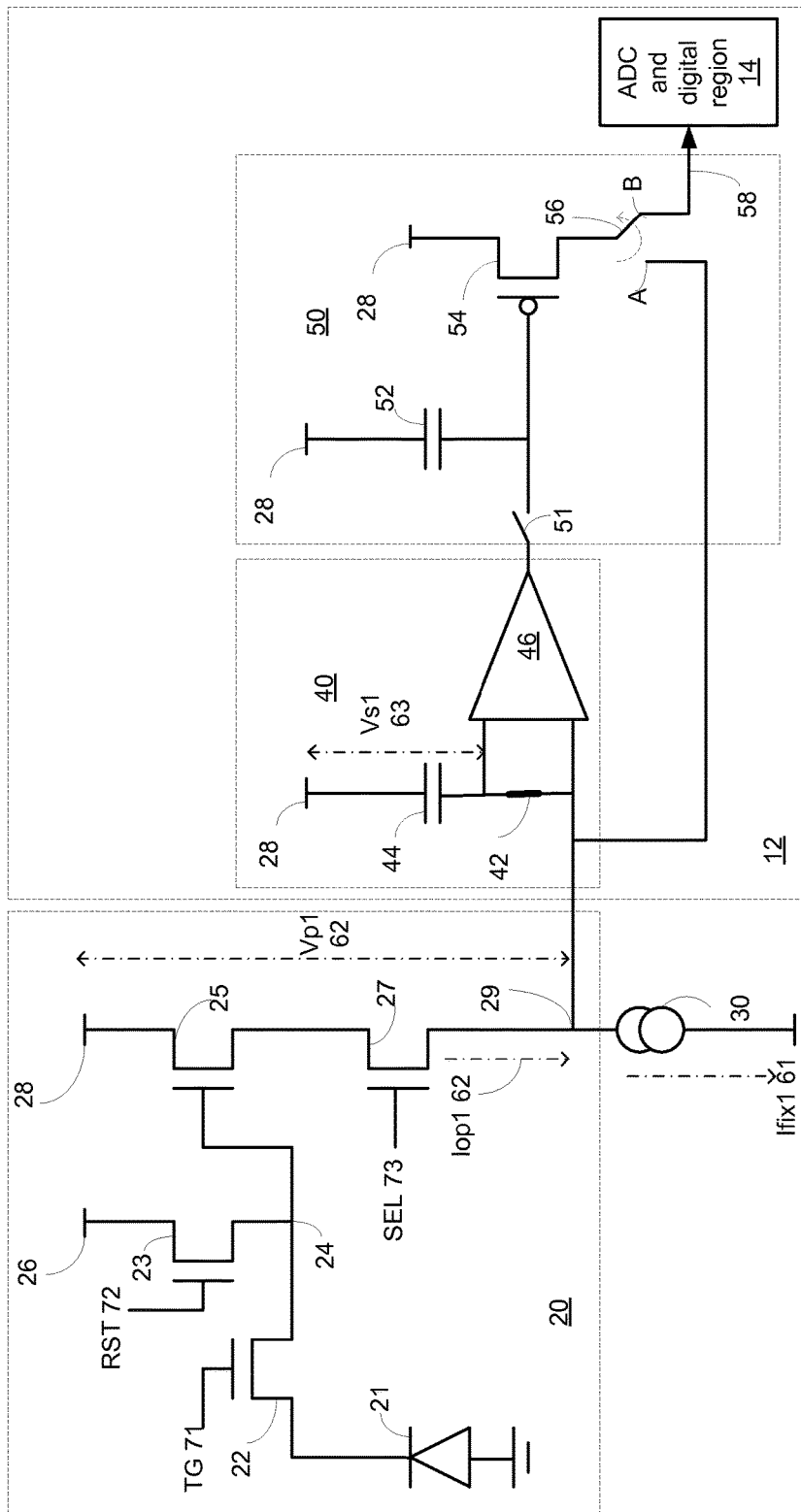
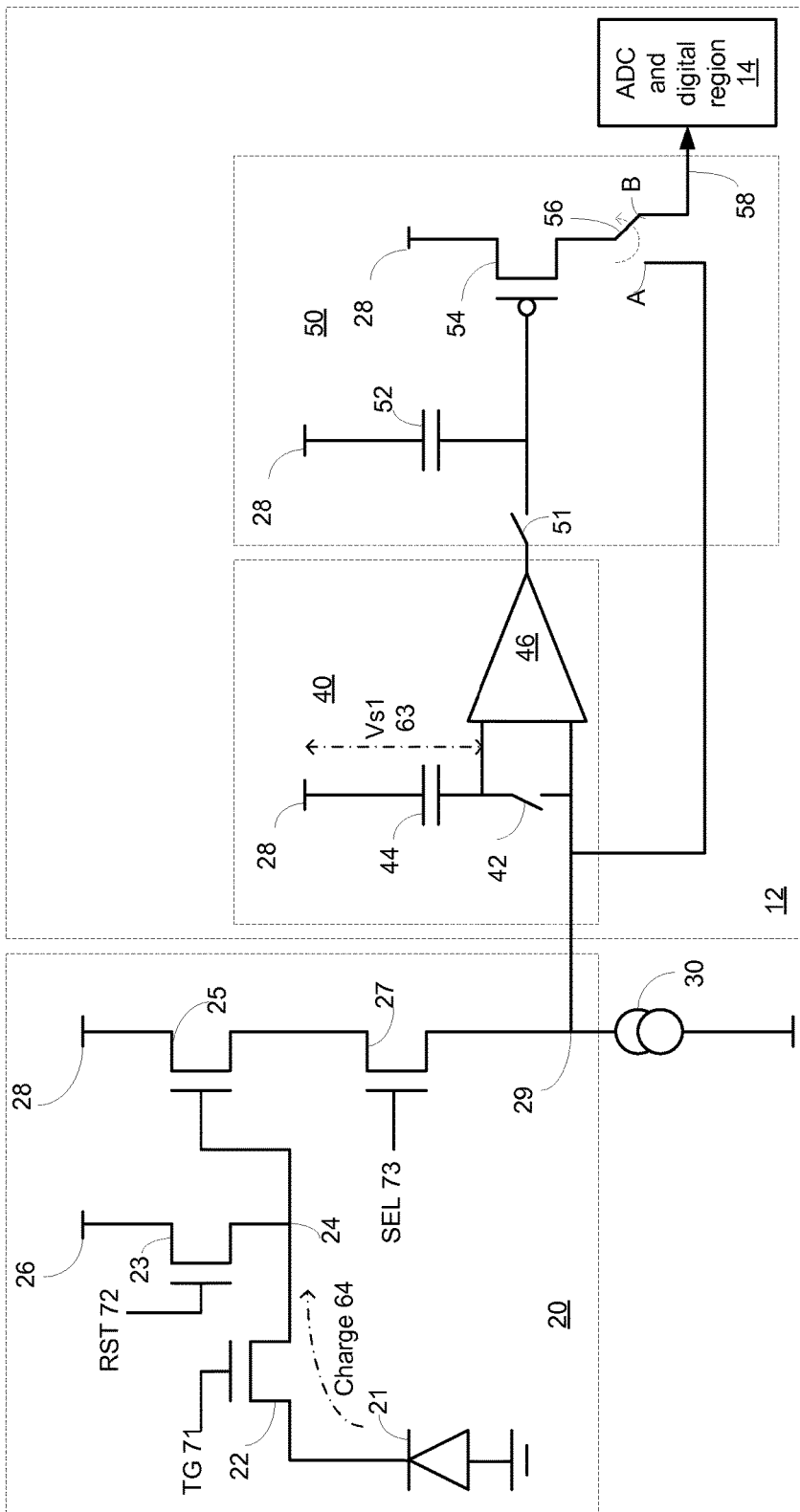


FIG. 1



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FIG. 2

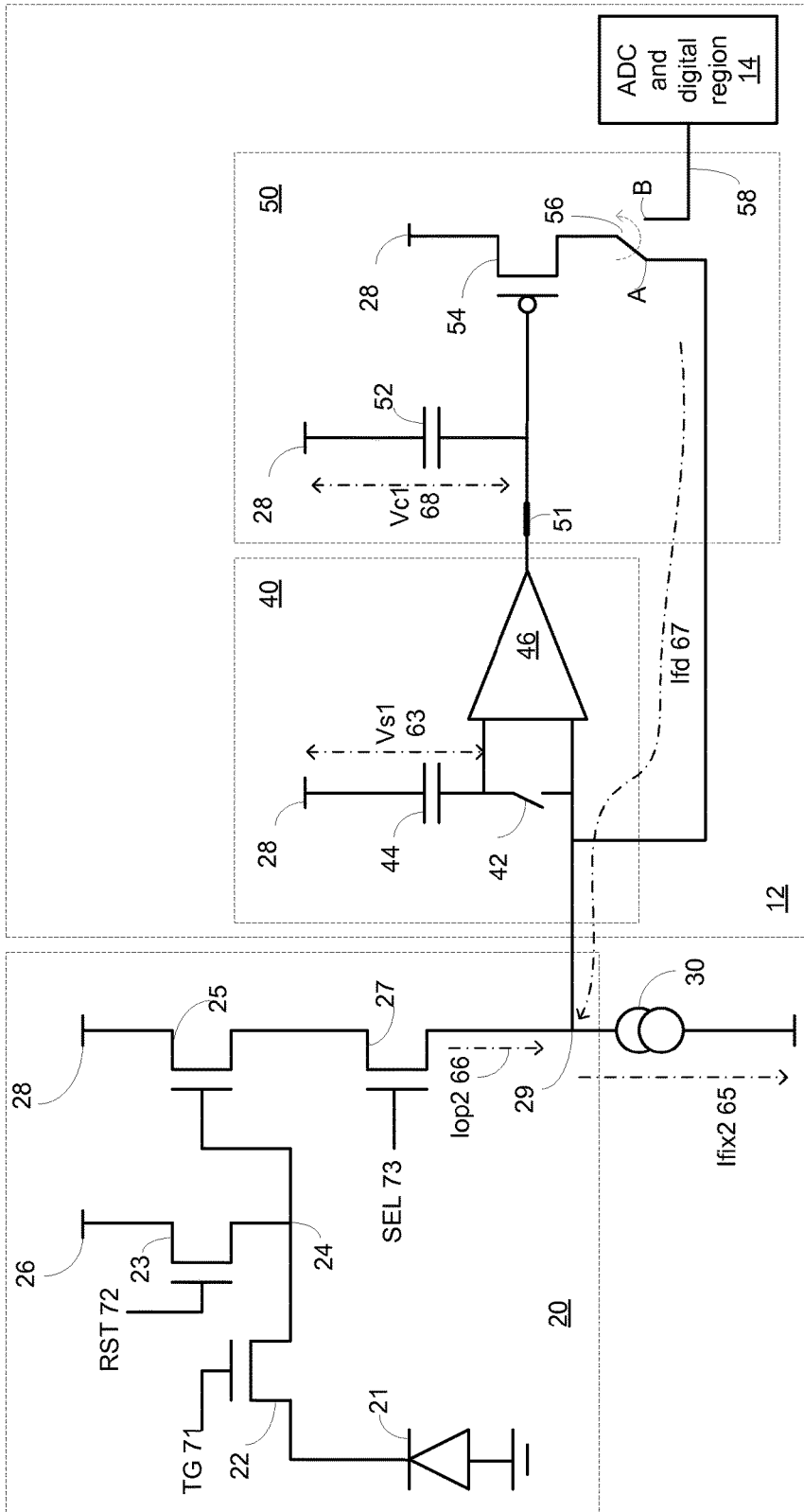


FIG. 3

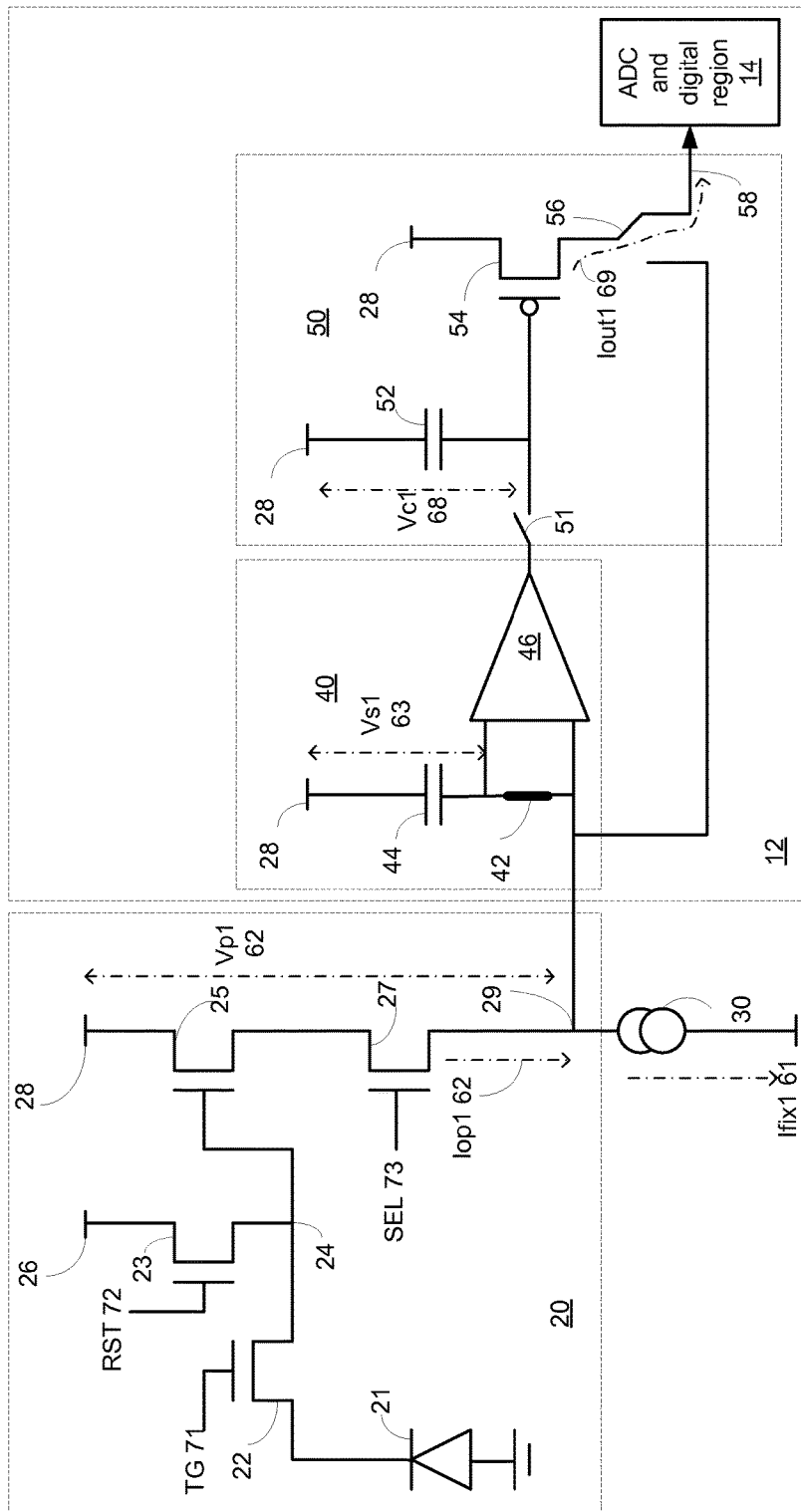


FIG. 4

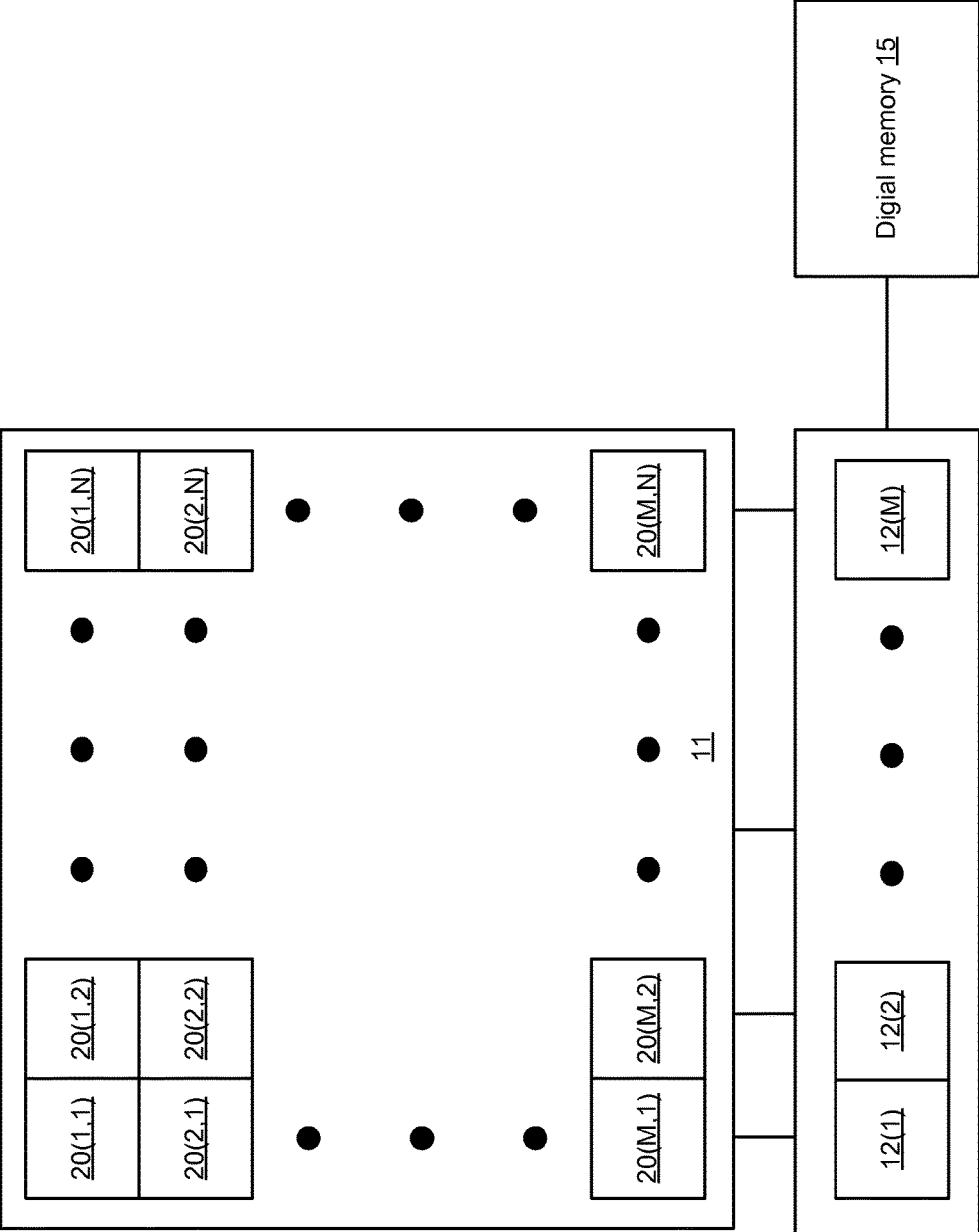


FIG. 5

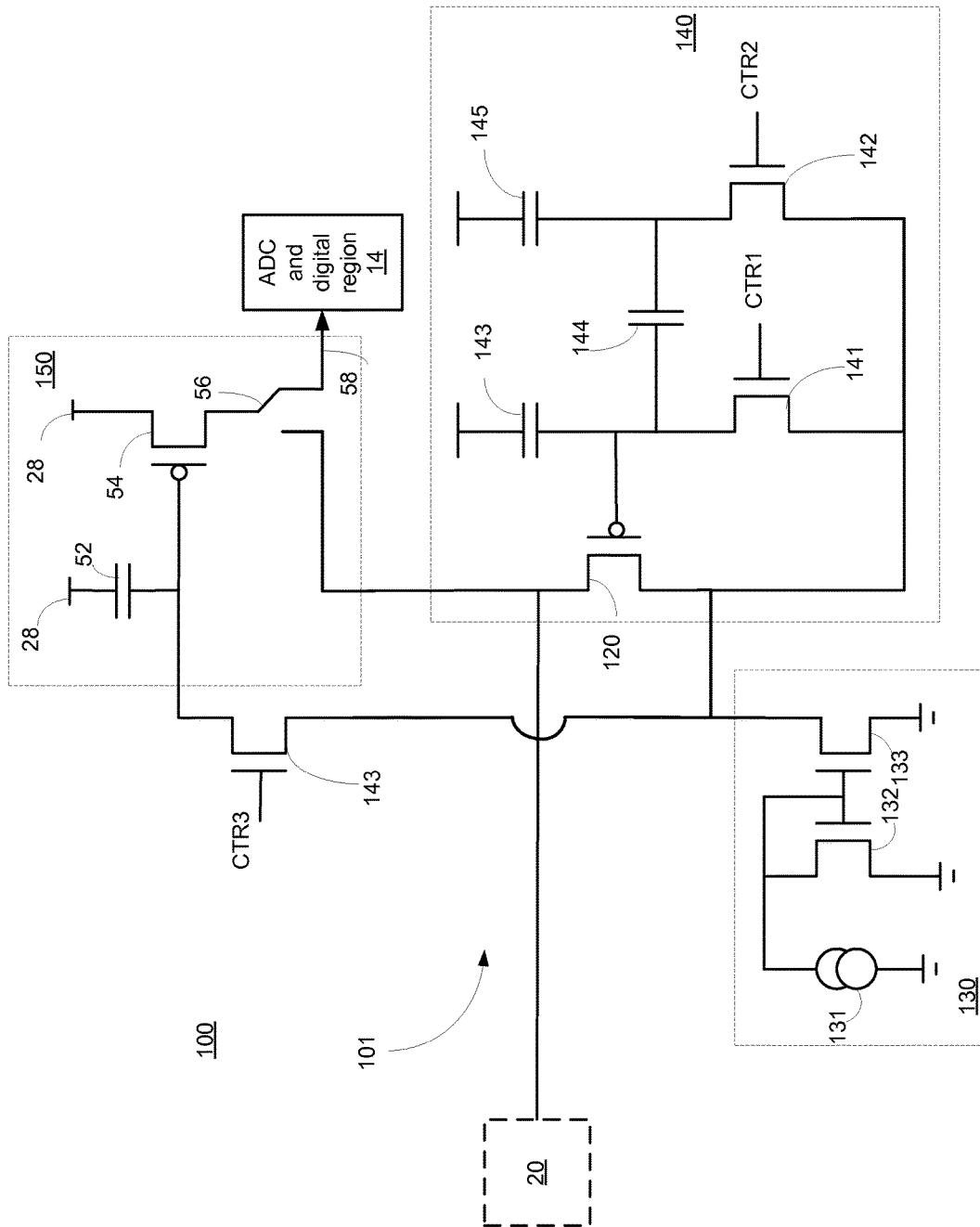


FIG. 6

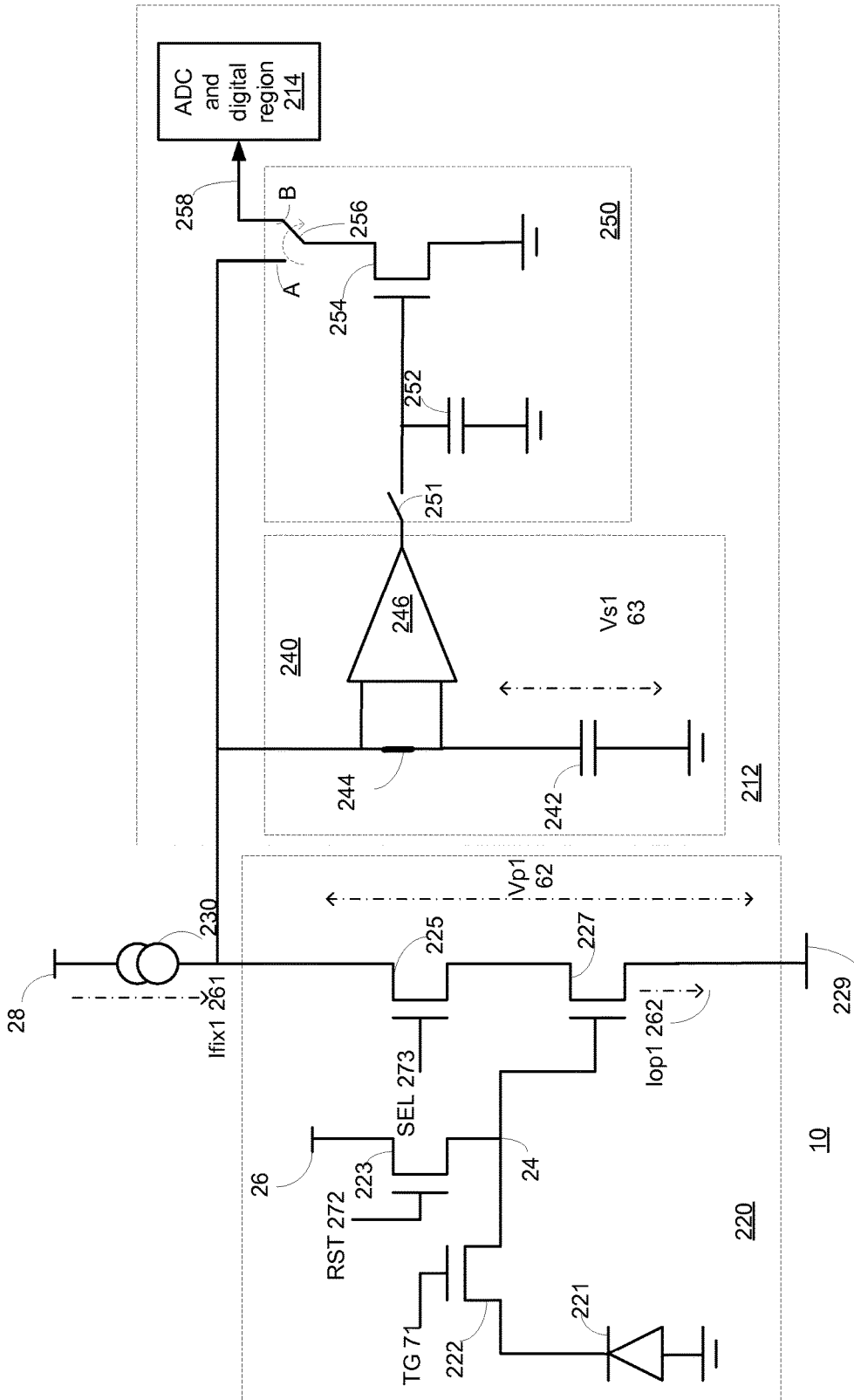


FIG. 7





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## CURRENT MODE PIXEL AND READOUT CIRCUIT HAVING A FIRST AND A SECOND READOUT PHASE

### BACKGROUND

Pixels are used to sense incoming radiation. Non-limiting examples of such pixels include infrared pixels, visible light pixels and various other radiation sensitive pixels.

Some pixels operate in a current mode while some other pixels operate in a voltage mode. A pixel that operates in current mode outputs an output current while a pixel that operates in voltage mode outputs an output voltage.

Pixels that operate in current mode have higher photore-  
sponse variations than pixels that operate in voltage mode—  
due to local variations of their output device transduc-  
tance. Due to these variations, most analog pixels operate at  
voltage mode although voltage mode is much slower than  
current mode.

### SUMMARY

According to an embodiment of the invention there may  
be provided a device that may include a pixel, a current  
source, and a readout circuit; during a first readout phase of  
the pixel, the readout circuit may be configured to sample a  
sampled output voltage of an output node of the pixel; and  
wherein an output current of the pixel is set by the current  
source; between the first readout phase of the pixel and a  
second readout phase of the pixel, the pixel may be config-  
ured to change the output current to provide a second output  
current, wherein the change of the output current is respon-  
sive to radiation sensed by a radiation sensor of the pixel  
during a sensing period; during the second readout phase of  
the pixel the readout circuit may be configured to sample the  
second output current while providing the sampled output  
voltage to the output node of the pixel; during the first  
readout phase of the pixel and the second readout phase of  
the pixel a drain source voltage of an output transistor of the  
pixel is maintained constant; and wherein the output trans-  
istor may be configured to generate the second output  
current.

The readout circuit may include a sample and buffer  
circuit and a current memory; wherein during the first  
readout phase the current memory is disconnected from the  
sample and buffer circuit and from the pixel.

During the second readout phase the current memory may  
be configured to provide to the output node of the pixel a  
feedback current that equals a difference between the second  
output current and a fixed current drained from the output  
node of the pixel by the current source.

The current memory may include a sampling unit and an  
output transistor; wherein the sampling component may be  
configured to sample, during the second readout phase, a  
sampled gate voltage of the output transistor; wherein the  
feedback current is provided to the output node of the pixel  
via a feedback loop; and wherein the sampling unit may be  
configured to provide to the gate of the output transistor the  
sampled gate voltage after the current memory is discon-  
nected from the pixel.

The current memory may include a current memory input  
switch, a feedback switch and a current memory output  
switch; wherein during the first readout phase the current  
memory input switch and the current memory output switch  
are closed and the feedback switch is open; wherein during

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the second readout phase the current memory input switch  
and the current memory output switch are open and the  
feedback switch is closed.

The sample and buffer circuit may include a first switch,  
an operational amplifier and a capacitor; wherein the capaci-  
tor may be coupled between an inverting input of the  
operational amplifier and a first end of the first switch;  
wherein a non-inverting input of the operational amplifier  
may be coupled to the output node of the pixel and to a  
second end of the first switch; wherein the first switch is  
closed during the first readout phase and is open during the  
second readout phase.

The sample and buffer circuit may include a first switch,  
an operational amplifier and a capacitor; wherein the capaci-  
tor may be coupled between an inverting input of the  
operational amplifier and a first end of the first switch;  
wherein a non-inverting input of the operational amplifier  
may be coupled to the output node of the pixel and to a  
second end of the first switch; wherein the first switch is  
closed during the first readout phase and is open during the  
second readout phase.

The current memory may be configured to output the  
sampled second output current to a digital region of the  
readout circuit during a next first readout phase that fol-  
lowed the second readout phase.

During the first readout phase of the pixel and the second  
readout phase of the pixel the drain source voltage of the  
output transistor is smaller than a difference between a gate  
drain voltage ( $V_{gs}$ ) of the output transistor and a threshold  
voltage  $V_{th}$  of the output transistor.

The a gate of the output transistor may be coupled to a  
floating diffusion node of the pixel; wherein between the first  
readout phase and the second readout phase, the pixel may  
be configured to transfer, to the floating diffusion node,  
charge that is responsive to the radiation sensed by the  
radiation sensor of the pixel during the sensing period.

The current source may be configured to drain, during the  
first readout phase of the pixel, a first fixed current and may  
be configured to drain, during the second readout phase of  
the pixel a second fixed current; wherein the second fixed  
current differs from the first fixed current.

The device may include set of pixels; wherein the readout  
circuit may be configured to perform a set of first readout  
phases for reading each pixel of the set of pixels and then to  
perform a set of second readout phases for reading each  
pixel of the set of pixels.

The readout circuit may include a set of sampling com-  
ponents for sampling, during the set of first readout phases,  
sampled output voltages of a set of output nodes of the set  
of pixels.

The current source may be coupled between a voltage  
supply and a select transistor of the pixel.

The output transistor may be coupled between the ground  
and the select transistor of the pixel.

The output transistor may be coupled between a voltage  
supply of less than 0.5 volts and the select transistor of the  
pixel.

The readout circuit may include a sample and buffer  
circuit and a current sampling circuit that may be configured  
to sample, during the second readout phase, a difference  
between the second output current and fixed supplied by the  
current source, wherein during a next first readout phase the  
current sampling circuit may be configured to output a signal  
that is responsive difference (the difference between the  
second output current and fixed supplied by the current  
source that was sampled during the second readout phase).

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According to an embodiment of the invention there may be provided a device that may include a pixel, a current source, a sample and buffer circuit and a current memory circuit; wherein during a first readout phase the current source may be configured to drain a first fixed current from an output node of the pixel, wherein the sample and buffer circuit may be configured to sample a voltage of the output node of the pixel to provide a sampled voltage, and the current source is disconnected from the sample and buffer circuit and from the output node of the pixel; wherein the pixel may be configured to transfer, between the first readout phase and a second readout phase, toward an output transistor of the pixel, a charge that is indicative of radiation sensed by the a sensing element of the pixel; wherein the output transistor of the pixel may be coupled to the output node of the pixel; wherein during a second readout phase the pixel may be configured to provide to the output node a pixel current that is responsive to the charge, the current source may be configured to drain a second fixed current from the output node of the pixel, the sample and buffer circuit may be configured to provide to the output node of the pixel the sampled voltage, and the current memory may be configured to provide, via a feedback path, a feedback current to the output node of the pixel and to store a current memory voltage that once provided to an output transistor of the current memory causes the current memory to output the feedback current; wherein the feedback current substantially equals a difference between the second fixed current and the pixel current; and wherein during a third readout phase the current memory may be configured to output the feedback current to a digital to analog converter.

#### BRIEF DESCRIPTION OF THE DRAWINGS

The subject matter regarded as the invention is particularly pointed out and distinctly claimed in the concluding portion of the specification. The invention, however, both as to organization and method of operation, together with objects, features, and advantages thereof, may best be understood by reference to the following detailed description when read with the accompanying drawings in which:

FIG. 1 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention;

FIG. 2 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention;

FIG. 3 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention;

FIG. 4 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention;

FIG. 5 illustrates a device that includes an array of pixels and an array of readout circuits according to an embodiment of the invention;

FIG. 6 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention; and

FIG. 7 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention; and

FIG. 8 illustrates a device that includes a pixel and readout circuit according to an embodiment of the invention.

#### DETAILED DESCRIPTION OF THE DRAWINGS

In the following detailed description, numerous specific details are set forth in order to provide a thorough understanding of the invention. However, it will be understood by those skilled in the art that the present invention may be

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practiced without these specific details. In other instances, well-known methods, procedures, and components have not been described in detail so as not to obscure the present invention.

The subject matter regarded as the invention is particularly pointed out and distinctly claimed in the concluding portion of the specification. The invention, however, both as to organization and method of operation, together with objects, features, and advantages thereof, may best be understood by reference to the following detailed description when read with the accompanying drawings.

It will be appreciated that for simplicity and clarity of illustration, elements shown in the figures have not necessarily been drawn to scale. For example, the dimensions of some of the elements may be exaggerated relative to other elements for clarity. Further, where considered appropriate, reference numerals may be repeated among the figures to indicate corresponding or analogous elements.

Because the illustrated embodiments of the present invention may for the most part, be implemented using electronic components and circuits known to those skilled in the art, details will not be explained in any greater extent than that considered necessary as illustrated above, for the understanding and appreciation of the underlying concepts of the present invention and in order not to obfuscate or distract from the teachings of the present invention.

Any reference in the specification to a method should be applied mutatis mutandis to a system capable of executing the method.

Any reference in the specification to a system should be applied mutatis mutandis to a method that may be executed by the system.

According to various embodiment of the invention there is provided a device that includes a current source, a readout circuit and a pixel. The readout circuit is configured to sample during a first readout phase an output voltage of the pixel while the output current of the pixel is set by the current source. During a second readout phase the readout circuit is configured to provide the sampled voltage (or a close approximation) to the pixel and sample an output current that represents radiation sensed by the pixel. This sampling as well as maintaining an output transistor of the pixel as certain bias causes the transconductance of the pixel to be essentially constant and mostly independent of pixel transistor parameters variations.

Any type of sampling may be applied during the first readout phase and the second readout phase. For example any sampling step that may mitigate noises such as thermal noise, supply noise, clock jitter or any other noises may be applied. The sampling may mitigate also different sources of sampling errors, such charge injection in switches, control signals feedthrough, or any other sources of static or dynamic errors.

The device may be a sensor, a camera, a communication device, a computer, a monitor, a media player, and the like.

In the following figures there are provided non-limiting examples of sample and buffer circuits and current memory.

FIG. 1 illustrates a device 10 that includes a pixel 20, current source 30 and readout circuit 12 during a first readout phase according to an embodiment of the invention. FIG. 2 illustrates device 10 during a period between the first readout phase and a second readout phase according to an embodiment of the invention. FIG. 3 illustrates device 10 during the second readout phase according to an embodiment of the invention. FIG. 4 illustrates device 10 during a next readout phase according to an embodiment of the invention.

Device **10** may include any type of pixel. Pixel **20** is a non-limiting example of a pixel. It is termed a 4T pixel as it includes four transistors. Pixel **20** may include three transistors or have more than four transistors.

Pixel **20** includes a photodiode **21**, a transfer gate transistor **22**, a reset transistor **23** a select transistor **27** and an output transistor **25**. The gate of transfer gate transistor **22** is fed by transfer gate control signal TG **71**. The gate of reset transistor **23** is fed by reset signal RST **72**, the gate of select transistor **27** is fed by select signal SEL **73** and the gate of output transistor **25** is coupled to a floating diffusion node **24** of pixel **20**.

The source of select transistor **27** is coupled to the output node **29** of pixel **20**.

Readout circuit **12** includes sample and buffer circuit **40**, current memory **50** and may or may not include analog to digital conversion (ADC) and digital region **14**.

Sample and buffer circuit **40** includes capacitor **44** and operational amplifier **46**. First switch **42** is connected between the inverting and non-inverting inputs of operational amplifier **46**. Second switch **51** is illustrated as being included in current memory **50** and is used to connect or disconnect current memory **50** from sample and buffer circuit **40**.

Current memory **50** includes capacitor **52** and output transistor **54**. The drain of output transistor **54** is coupled a SPDT switching unit that include switch **56** that has a single input and two outputs A and B.

The drain of reset transistor **23** is coupled to first voltage source **26**. The source of output transistor **54** and the drain of output transistor **25** are coupled to a second voltage source **28**. The second voltage source **28** may supply a voltage that is lower than the voltage of first voltage supply **26**. Thus, output transistor **25** may be maintained in its linear region and far away from its saturation region.— In another embodiment of the invention, voltage sources **26** and **28** can be implemented as one source whose voltage just changes between reset and read operation. This avoids the need to bring separate metal lines for the above mentioned voltages to the pixel.

For example, first voltage source **28** may supply between 2.7 volts to 5 volts while second voltage source **28** may supply about 0.95 volts.

During a first readout phase of pixel **20**, the readout circuit **12** is configured to sample a sampled output voltage  $V_{p1}$  **62** of output node **29**. Capacitor **44** of sample and buffer circuit **40** samples  $V_{s1}$  **63**= $V_{p1}$  **62**.

Switch **56** is at its B position.

During the first readout phase output node **29** is disconnected from the current memory **50** and the current that flows through output node **29** equals the current  $I_{fix1}$  **61** drained by current source **30**.  $I_{fix1}$  **61** sets the current (source drain current) outputted by output transistor **25**.

FIG. **2** illustrates the transfer of charge **64** between photodiode **21** and floating diffusion node **24**. The transfer occurs between the first readout phase of the pixel and a second readout phase of pixel **20**. The charge **64** affects the conductivity of output transistor **25** and output transistor **25** outputs a current that differs from  $I_{fix1}$  **61** and reflects charge **64**. Usually, charge **64** reduces the conductivity of output transistor **25** thereby reducing the source drain current outputted by output transistor **25**.

As indicated above, between the first and second readout phases pixel **20** is configured to change the output current (outputted by output transistor **25**) to provide a second

output current. The change of the output current is responsive to radiation sensed by a radiation sensor of the pixel during a sensing period.

FIG. **3** illustrates that during the second readout phase of the pixel, first switch **42** is disconnected, second switch **51** connects current memory **50** to sample and buffer circuit **40**. Switch **56** is at position A thereby closing a feedback loop to output node **29**.

Capacitor **44** stores  $V_{s1}$  **63** (sampled during the first readout phase).

Due to charge **64** the output current from pixel **20**  $I_{op}$  **66** is smaller than the current  $I_{fix2}$  **65** drained by current source **30**. Current memory **50** supplies to the output node **29**, via the feedback loop, feedback current  $I_{fd}$  **67** that equals the difference between the second output current  $I_{op2}$  **66** and  $I_{fix2}$  **65**. Capacitor **52** stores the voltage that once applied to the gate of output transistor **54** causes the output transistor to output  $I_{fd}$  **67**.

$I_{fix1}$  may equal  $I_{fix2}$ . Alternatively,  $I_{fix2}$  may be larger than  $I_{fix1}$  in order to allow a flow of a feedback current event when charge **64** is zero—thereby providing a bias to the feedback loop and allowing a convergence of the feedback loop.

During the second readout phase capacitor **44** feeds operational amplifier **46** with a voltage sampled during the first readout phase.

FIG. **4** illustrates that during the next first readout phase the current memory **50** outputs to ADC and digital region **14** an output current  $I_{out1}$  **69** that equals  $I_{fd}$  **67**. During the next first readout phase the sample and buffer circuit may sample the voltage of output node **29**. The output current  $I_{out1}$  represents charge **64** that in turn represents the radiation sensed by pixel **20**.

According to an embodiment of the invention each set of pixels may be selectively coupled to a readout circuit. The readout circuit may operate in a pipelined manner during which the readout circuit performs a set of first readout phases (for different pixels) that is followed by a set of second readout phases (for different pixels).

This pipelined operation allows increasing the time between the first and second readout phase of each pixel and this may be useful when the transfer of charge from the photodiode to the floating transfer node is longer than the duration of the first and/or second readout phases.

In the readout circuit one or more pixels may share (or not share) a current source while each pixels is associated with a separate sample and buffer circuit and a separate current memory.

FIG. **5** illustrates a two dimensional array **11** of pixels **20(1,1)-20(M,N)**, an array of readout circuits **12(1)-12(M)**—one per column of two dimensional array **11** and digital memory **15**.

FIG. **6** illustrates pixel **20**, current source **130** and a readout circuit **101** according to an embodiment of the invention.

Current source **130** includes current source **131** and a current mirror that is formed from transistors **132** and **133**. Any type of current source capable of providing a fixed current may be provided.

The sample and buffer circuit **140** is built around amplifier **120** that includes a single transistor.

Sample and buffer circuit **140** includes first switch **141**, second switch **142**, first capacitor **143**, second capacitor **145** and intermediate capacitor **144**.

First switch **141** is fed by control signals **CTR1**, second switch **142** is fed by control signals **CTR2**. A third switch **143** is fed by control signals **CTR3** and performs a similar function to switch **51**.

Intermediate capacitor **144** provides a weak coupling between first capacitor **143** and second capacitor **145**. The two phase sampling performed by switches **141** and **142** reduces the noise contribution of the sampling.

A similar sampling noise reducing process can be applied during the second readout phase.

During the first readout phase the following sub-phases may be executed:

- a) First switch **141** and second switch **142** are closed to sample the output voltage of pixel **20**.
- b) First switch **141** is opened thereby introducing a voltage error that changes the voltage of first capacitor **143**. Second switch **142** is still closed thus closing a feedback loop with amplifier **120**, and intermediate capacitor **144**. This feedback loop compensates for the voltage error.
- c) Second switch **142** is opened thereby introducing a much smaller voltage error in the voltage of first capacitor **143**—due to the weak coupling (for example a 1:10 coupling) introduced by intermediate capacitor **144**.

Variants of this sampling noise reduction technique that employ more than two sub-phases and use capacitor-switch ladders with more steps in order to achieve further reduction in noise contribution are possible.

Current memory circuit **50** (**150**) may be substituted by any other type of current sampling circuit (such as sampling circuit **250** of FIG. **8**) that may be an integrator circuit, the current sampling circuit **250** may be configured to, during the second readout phase, integrate the current **Idf 67** and during the next first readout phase output a signal that represents this current integral.

FIG. **7** illustrates pixel **220**, current source **230** and readout circuit **212** according to an embodiment of the invention.

Pixel **220** is an example of a variant of a 4T pixel in which the source of output transistor **227** is connected to voltage **229** that is a voltage close to but higher than the ground. The source of select transistor **225** is connected to the drain of output transistor **227**. The drain of select transistor **225** is connected to the output conductor **229**. Current flow direction in the output section of pixel **220** is reversed relative to the current direction in pixel **20**, thus permitting use of higher currents and thus achieving faster readout times.

Readout circuit **212** comprises of sample and buffer circuit **240**, current memory circuit **250** and may or may not include ADC and digital region **214**. Current flow direction in circuits **240** and **250** is reversed relative to current flow direction in circuits **40** and **50** in order to match current flow direction in pixel **220**.

In the foregoing specification, the invention has been described with reference to specific examples of embodiments of the invention. It will, however, be evident that various modifications and changes may be made therein without departing from the broader spirit and scope of the invention as set forth in the appended claims.

Moreover, the terms “front,” “back,” “top,” “bottom,” “over,” “under” and the like in the description and in the claims, if any, are used for descriptive purposes and not necessarily for describing permanent relative positions. It is understood that the terms so used are interchangeable under appropriate circumstances such that the embodiments of the

invention described herein are, for example, capable of operation in other orientations than those illustrated or otherwise described herein.

Those skilled in the art will recognize that the boundaries between logic blocks are merely illustrative and that alternative embodiments may merge logic blocks or circuit elements or impose an alternate decomposition of functionality upon various logic blocks or circuit elements. Thus, it is to be understood that the architectures depicted herein are merely exemplary, and that in fact many other architectures may be implemented which achieve the same functionality.

Any arrangement of components to achieve the same functionality is effectively “associated” such that the desired functionality is achieved. Hence, any two components herein combined to achieve a particular functionality may be seen as “associated with” each other such that the desired functionality is achieved, irrespective of architectures or intermedial components. Likewise, any two components so associated can also be viewed as being “operably connected,” or “operably coupled,” to each other to achieve the desired functionality.

Furthermore, those skilled in the art will recognize that boundaries between the above described operations merely illustrative. The multiple operations may be combined into a single operation, a single operation may be distributed in additional operations and operations may be executed at least partially overlapping in time. Moreover, alternative embodiments may include multiple instances of a particular operation, and the order of operations may be altered in various other embodiments.

Also for example, in one embodiment, the illustrated examples may be implemented as circuitry located on a single integrated circuit or within a same common mode noise choke. Alternatively, the examples may be implemented as any number of separate integrated circuits or separate common mode noise chokes interconnected with each other in a suitable manner.

However, other modifications, variations and alternatives are also possible. The specifications and drawings are, accordingly, to be regarded in an illustrative rather than in a restrictive sense.

In the claims, any reference signs placed between parentheses shall not be construed as limiting the claim. The word ‘comprising’ does not exclude the presence of other elements or steps than those listed in a claim. Furthermore, the terms “a” or “an,” as used herein, are defined as one or more than one. Also, the use of introductory phrases such as “at least one” and “one or more” in the claims should not be construed to imply that the introduction of another claim element by the indefinite articles “a” or “an” limits any particular claim containing such introduced claim element to inventions containing only one such element, even when the same claim includes the introductory phrases “one or more” or “at least one” and indefinite articles such as “a” or “an.” The same holds true for the use of definite articles. Unless stated otherwise, terms such as “first” and “second” are used to arbitrarily distinguish between the elements such terms describe. Thus, these terms are not necessarily intended to indicate temporal or other prioritization of such elements. The mere fact that certain measures are recited in mutually different claims does not indicate that a combination of these measures cannot be used to advantage.

Any reference to the term “comprising” or “having” should be interpreted also as referring to “consisting” of “essentially consisting of”. For example—a device that comprises certain components can include additional components, can be limited to the certain components or may

include additional components that do not materially affect the basic and novel characteristics of the device—respectively.

While certain features of the invention have been illustrated and described herein, many modifications, substitutions, changes, and equivalents will now occur to those of ordinary skill in the art. It is, therefore, to be understood that the appended claims are intended to cover all such modifications and changes as fall within the true spirit of the invention.

We claim:

1. A device comprising a pixel, a current source, and a readout circuit;

wherein during a first readout phase of the pixel, the readout circuit is configured to sample a sampled output voltage of an output node of the pixel; and wherein an output current of the pixel is set by the current source;

wherein between the first readout phase of the pixel and a second readout phase of the pixel, the pixel is configured to change the output current to provide a second output current, wherein the change of the output current is responsive to radiation sensed by a radiation sensor of the pixel during a sensing period;

wherein during the second readout phase of the pixel the readout circuit is configured to sample the second output current while providing the sampled output voltage to the output node of the pixel;

wherein during the first readout phase of the pixel and the second readout phase of the pixel a drain source voltage of an output transistor of the pixel is maintained constant; and

wherein the output transistor is configured to generate the second output current.

2. The device according to claim 1 wherein the readout circuit comprises a sample and buffer circuit and a current memory; wherein during the first readout phase the current memory is disconnected from the sample and buffer circuit and from the pixel.

3. The device according to claim 2 wherein during the second readout phase the current memory is configured to provide to the output node of the pixel a feedback current that equals a difference between the second output current and a fixed current drained from the output node of the pixel by the current source.

4. The device according to claim 3 wherein the current memory comprises a sampling unit and an output transistor; wherein the sampling component is configured to sample, during the second readout phase, a sampled gate voltage of the output transistor; wherein the feedback current is provided to the output node of the pixel via a feedback loop; and wherein the sampling unit is configured to provide to the gate of the output transistor the sampled gate voltage after the current memory is disconnected from the pixel.

5. The device according to claim 2 wherein the current memory comprises a current memory input switch, a feedback switch and a current memory output switch; wherein during the first readout phase the current memory input switch and the current memory output switch are closed and the feedback switch is open; wherein during the second readout phase the current memory input switch and the current memory output switch are open and the feedback switch is closed.

6. The device according to claim 5 wherein the sample and buffer circuit comprises a first switch, an operational amplifier and a capacitor; wherein the capacitor is coupled between an inverting input of the operational amplifier and

a first end of the first switch; wherein a non-inverting input of the operational amplifier is coupled to the output node of the pixel and to a second end of the first switch; wherein the first switch is closed during the first readout phase and is open during the second readout phase.

7. The device according to claim 2 wherein the sample and buffer circuit comprises a first switch, an operational amplifier and a capacitor; wherein the capacitor is coupled between an inverting input of the operational amplifier and a first end of the first switch; wherein a non-inverting input of the operational amplifier is coupled to the output node of the pixel and to a second end of the first switch; wherein the first switch is closed during the first readout phase and is open during the second readout phase.

8. The device according to claim 2 wherein the current memory is configured to output the sampled second output current to a digital region of the readout circuit during a next first readout phase that followed the second readout phase.

9. The device according to claim 1 wherein during the first readout phase of the pixel and the second readout phase of the pixel the drain source voltage of the output transistor is smaller than a difference between a gate drain voltage ( $V_{gs}$ ) of the output transistor and a threshold voltage  $V_{th}$  of the output transistor.

10. The device according to claim 1 wherein a gate of the output transistor is coupled to a floating diffusion node of the pixel; wherein between the first readout phase and the second readout phase, the pixel is configured to transfer, to the floating diffusion node, charge that is responsive to the radiation sensed by the radiation sensor of the pixel during the sensing period.

11. The device according to claim 1 wherein the current source is configured to drain, during the first readout phase of the pixel, a first fixed current and is configured to drain, during the second readout phase of the pixel a second fixed current; wherein the second fixed current differs from the first fixed current.

12. The device according to claim 1 comprises set of pixels; wherein the readout circuit is configured to perform a set of first readout phases for reading each pixel of the set of pixels and then to perform a set of second readout phases for reading each pixel of the set of pixels.

13. The device according to claim 12 wherein the readout circuit comprise a set of sampling components for sampling, during the set of first readout phases, sampled output voltages of a set of output nodes of the set of pixels.

14. The device according to claim 1 wherein the current source is coupled between a voltage supply and a select transistor of the pixel.

15. The device according to claim 1 wherein the output transistor is coupled between the ground and the select transistor of the pixel.

16. The device according to claim 1 wherein the output transistor is coupled between a voltage supply of less than 0.5 volts and the select transistor of the pixel.

17. The device according to claim 1 wherein the readout circuit comprises a sample and buffer circuit and a current sampling circuit that is configured to sample, during the second readout phase, a difference between the second output current and fixed supplied by the current source, wherein during a next first readout phase the current sampling circuit is configured to output a signal that is responsive difference.

18. A device comprising a pixel, a current source, a sample and buffer circuit and a current memory circuit; wherein during a first readout phase the current source is configured to drain a first fixed current from an output

node of the pixel, wherein the sample and buffer circuit is configured to sample a voltage of the output node of the pixel to provide a sampled voltage, and the current source is disconnected from the sample and buffer circuit and from the output node of the pixel; 5

wherein the pixel is configured to transfer, between the first readout phase and a second readout phase, toward an output transistor of the pixel, a charge that is indicative of radiation sensed by the sensing element of the pixel; wherein the output transistor of the pixel is 10 coupled to the output node of the pixel;

wherein during a second readout phase the pixel is configured to provide to the output node a pixel current that is responsive to the charge, the current source is configured to drain a second fixed current from the 15 output node of the pixel, the sample and buffer circuit is configured to provide to the output node of the pixel the sampled voltage, and the current memory circuit is configured to provide, via a feedback path, a feedback current to the output node of the pixel and to store a 20 current memory voltage that once provided to an output transistor of the current memory circuit causes the current memory to output the feedback current; wherein the feedback current substantially equals a difference between the second fixed current and the 25 pixel current;

wherein during a third readout phase the current memory circuit is configured to output the feedback current to a digital to analog converter.

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